

NTS1545EMFS, NRVTS1545EMFS

Exceptionally Low Leakage Trench-based Schottky Rectifier

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

Typical Applications

- Switching Power Supplies including Wireless, Smartphone and Notebook Adapters
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

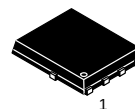


ON Semiconductor®

<http://onsemi.com>

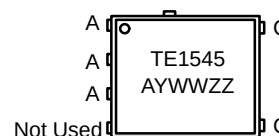
SCHOTTKY BARRIER RECTIFIERS 15 AMPERES 45 VOLTS

1,2,3  5,6



SO-8 FLAT LEAD
CASE 488AA
STYLE 2

MARKING DIAGRAM



TE1545 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTS1545EMFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NTS1545EMFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
NRVTS1545EMFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NRVTS1545EMFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTS1545EMFS, NRVTS1545EMFS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Forward Current (Rated V_R , $T_C = 165^\circ\text{C}$)	$I_{F(AV)}$	15	A
Peak Repetitive Forward Current, (Rated V_R , Square Wave, 20 kHz, $T_C = 164^\circ\text{C}$)	I_{FRM}	30	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	210	A
Storage Temperature Range	T_{stg}	-65 to +175	$^\circ\text{C}$
Operating Junction Temperature	T_J	-55 to +175	$^\circ\text{C}$
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E_{AS}	100	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Case, Steady State (Assumes 600 mm ² 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JC}$	1.3	–	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1) ($i_F = 5.0$ Amps, $T_J = 25^\circ\text{C}$) ($i_F = 7.5$ Amps, $T_J = 25^\circ\text{C}$) ($i_F = 15$ Amps, $T_J = 25^\circ\text{C}$) ($i_F = 5.0$ Amps, $T_J = 125^\circ\text{C}$) ($i_F = 7.5$ Amps, $T_J = 125^\circ\text{C}$) ($i_F = 15$ Amps, $T_J = 125^\circ\text{C}$)	V_F	0.44 0.46 0.50 0.33 0.36 0.43	– – 0.60 – – 0.53	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$)	i_R	– 15	50 20	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

TYPICAL CHARACTERISTICS

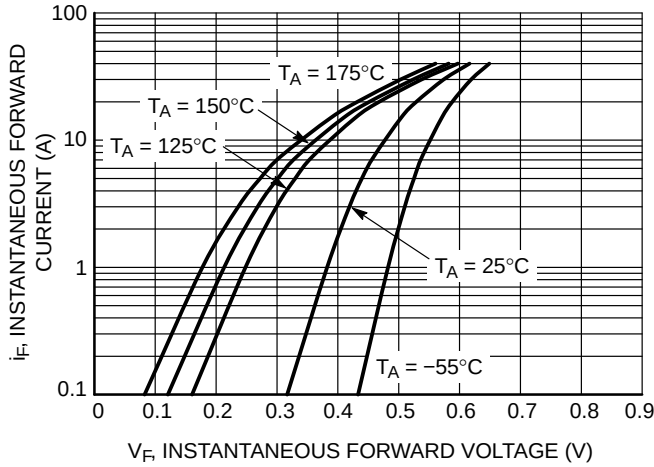


Figure 1. Typical Instantaneous Forward Characteristics

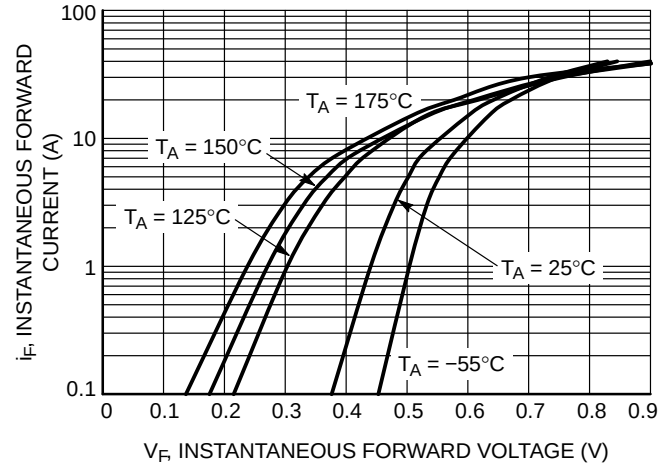


Figure 2. Maximum Instantaneous Forward Characteristics

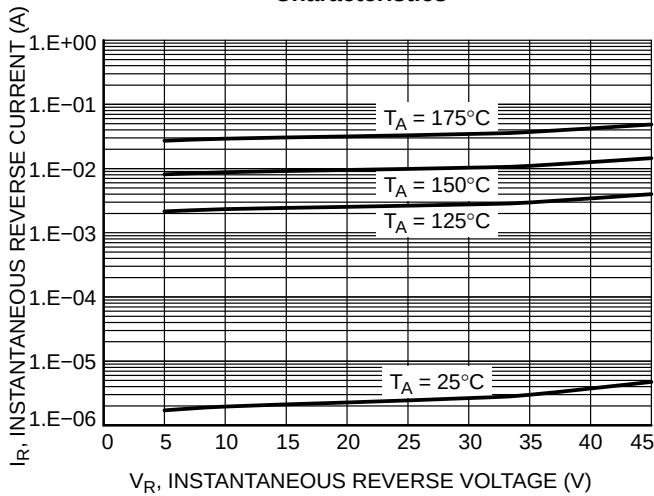


Figure 3. Typical Reverse Characteristics

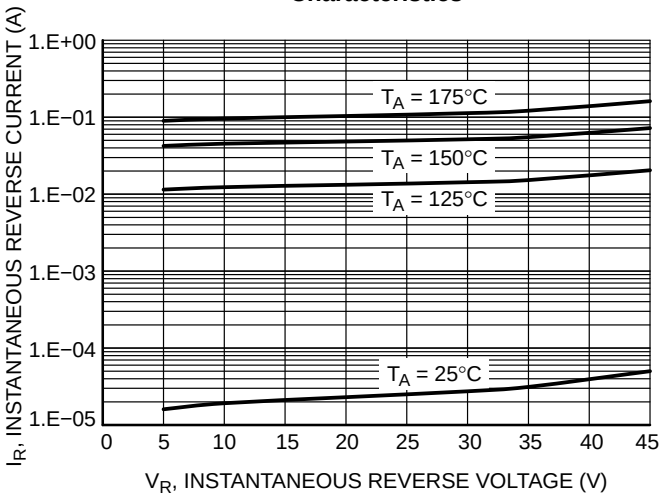


Figure 4. Maximum Reverse Characteristics

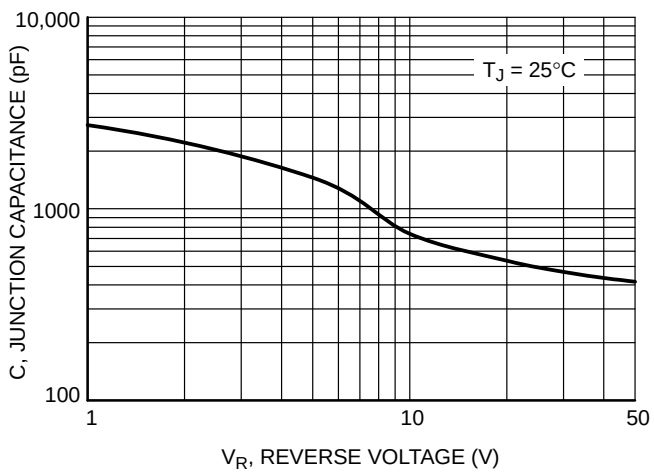


Figure 5. Typical Junction Capacitance

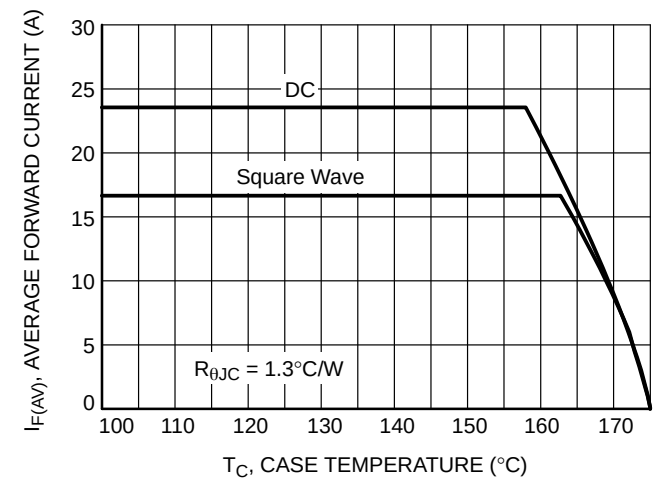


Figure 6. Current Derating

NTS1545EMFS, NRVTS1545EMFS

TYPICAL CHARACTERISTICS

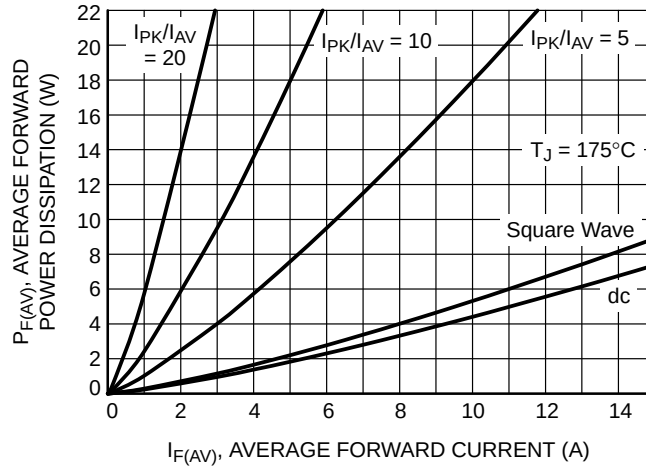


Figure 7. Forward Power Dissipation

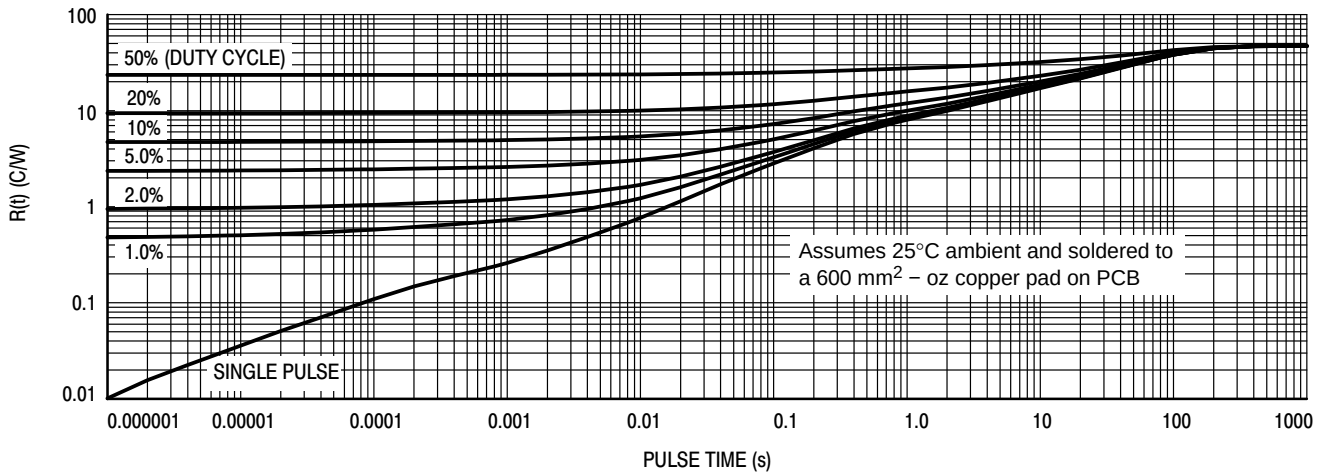


Figure 8. Typical Thermal Characteristics

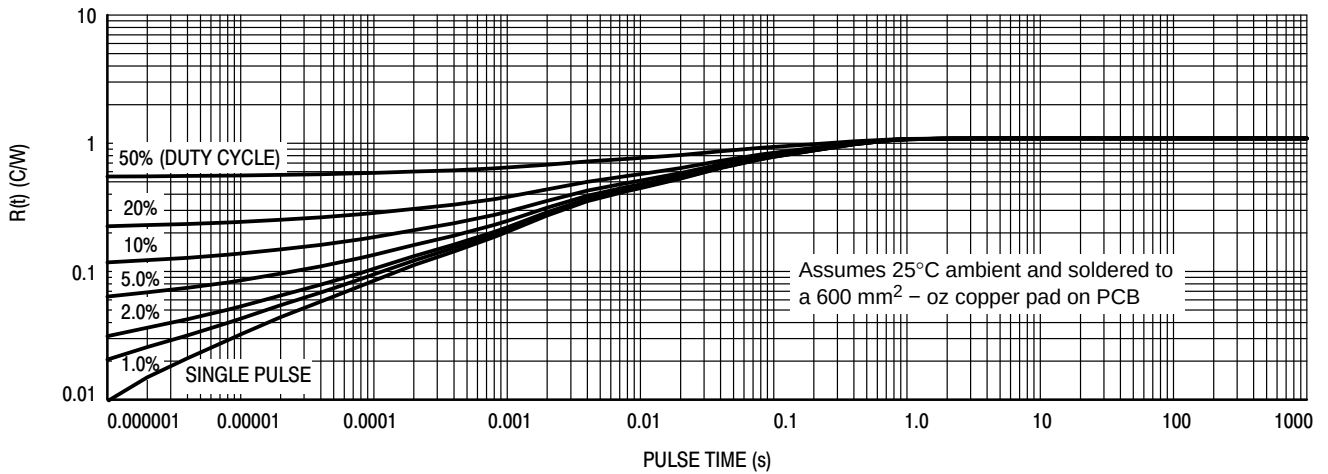


Figure 9. Typical Transient Thermal Response Characteristics, Junction-to-Case

NTS1545EMFS/D

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9